

SPUTTERING TARGET

ABSTRACT

Provided is a sputtering target with which it is possible to
5 form a magnetic thin film having a high coercive force H_c .

The sputtering target is a sputtering target that contains
metallic Co, metallic Pt, and an oxide, wherein the sputtering target
contains no metallic Cr except inevitable impurities, and the oxide
has a melting point of 600°C or lower and a standard Gibbs free energy
10 of formation ΔG_f of the oxide with respect to 1mol O_2 being $-1,000$
kJ/mol O_2 or more and -500 kJ/mol O_2 or less.

[Figure 2]